UVDI Technology Overview

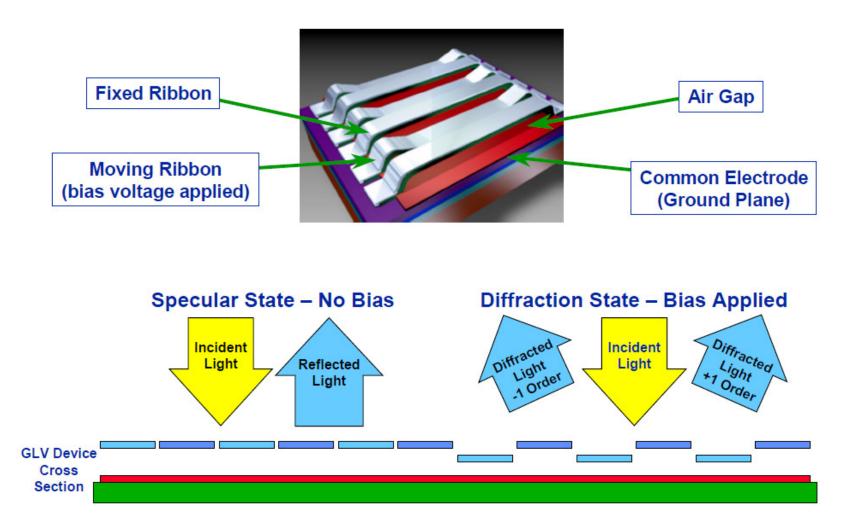


UltraViolet Direct Imaging based on

Integrated GLV Technology

Grating Light ValveTM Technology Spatial Light Modulation based on Diffraction





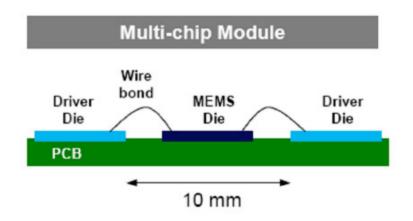
Integrated MEMS – What is it?

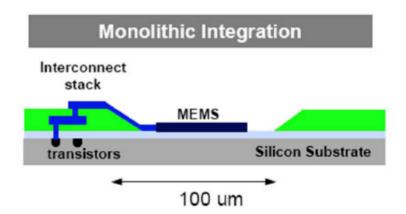


- "Integration" = CMOS + MEMS on the same chip
- MEMS devices must interface to outside world. These interfaces can fall into two general categories:
 - Multi-chip packaging solutions (multiple chips wire-bonded)
 - Monolithic integration solutions (single chip)
- Motivation for Integration:
 - Performance (high density, low parasitics, e.g., iGLV)
 - Cost (reduced component count)
- SLM is one of the few companies to successfully realize a fully integrated MEMS/CMOS device (iGLV)
 - 2006 SLM integrated GLV with Cypress Via-link 2.7 process
 - 2009 SLM is integrating GLV with Freescale SmartMOS07

Discrete and Integrated Solutions





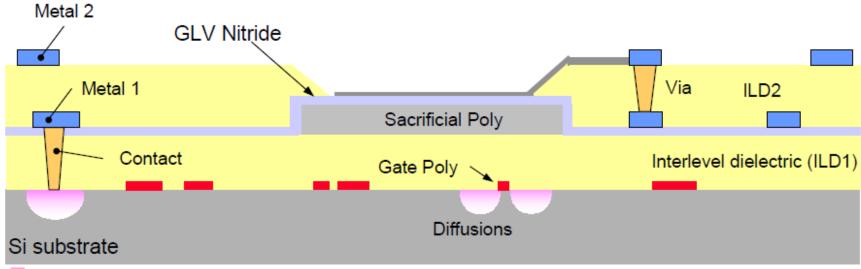


- Worked well for CtP application
 - 1088 channels
 - 28 mm die length
 - 25.5 um channel pitch

- Required because of UVDI channel count
 - 8192 channels
 - 41 mm die length
 - 5 um channel pitch

Integrated Process Flow



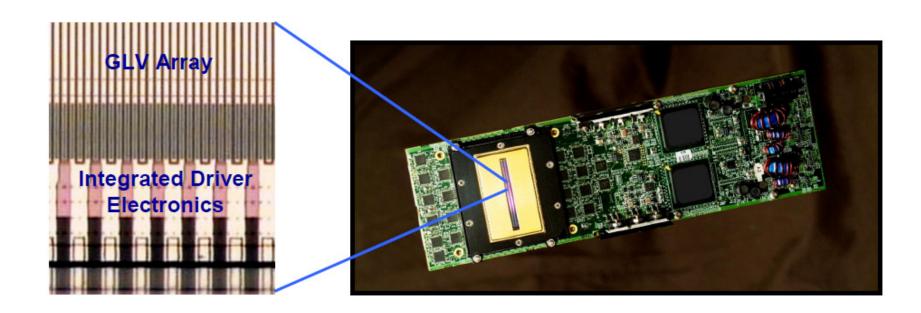


- Transistor diffusions are first.
- Poly-Si gate lines followed by first insulating oxide & polish (CMP)
- Contacts are drilled & filled. Surface is polished again.
- GLV sacrificial layer is deposited & patterned
- LPCVD silicon nitride ribbon deposition.
- Metal1 deposited & patterned, more dielectric, vias, and Metal2.
- GLV re-exposed with high-selectivity etching & final interconnect
- Final MEMS ribbon patterning. GLV complete

New 8K Integrated GLV Device



- GLV Linear array has 8192 addressable elements
- 12-14 bit Grayscale (independent of frame rate)
- Designed for UV applications



Direct-Write Lithography Applications



A SCREEN COMPANY

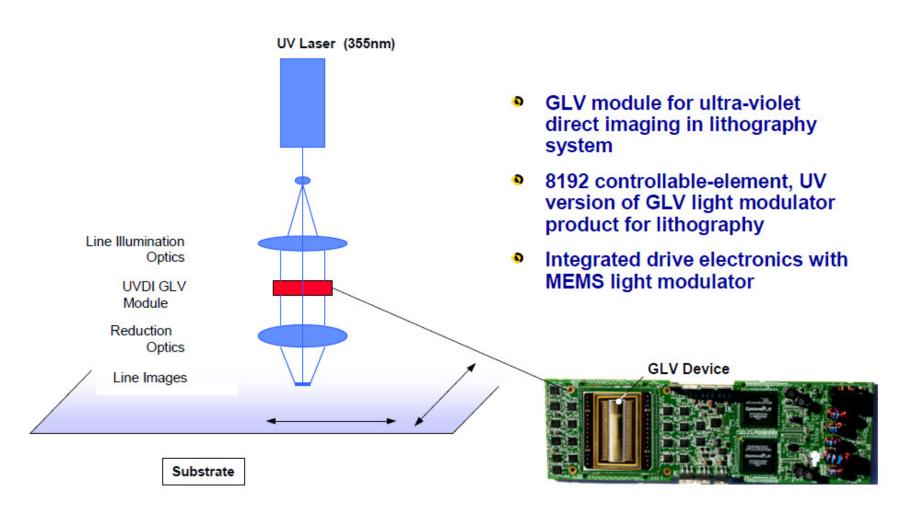
GLV™ Direct-Write Lithography



- Developed new, high pixel count Ultra Violet Digital Imaging (UVDI) GLV module
- Customer system currently in Beta trials in production fab
- UVDI module can be modified for visible (RGB) applications

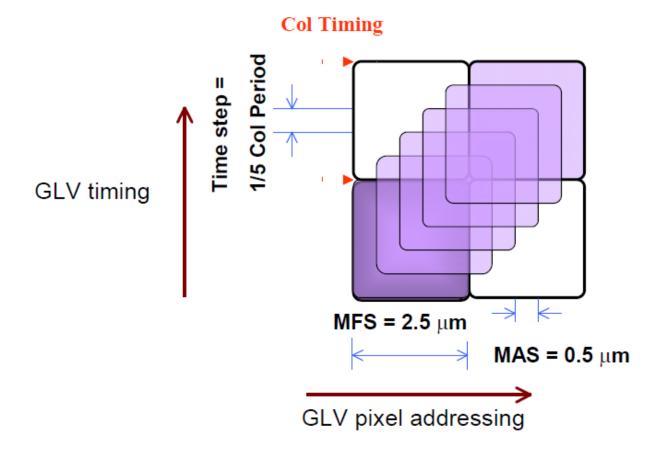
Maskless Lithography Using GLV









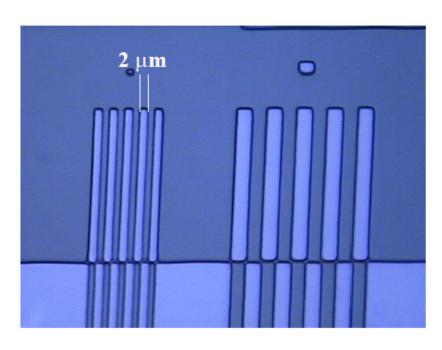


MFS:Minimum Feature Size

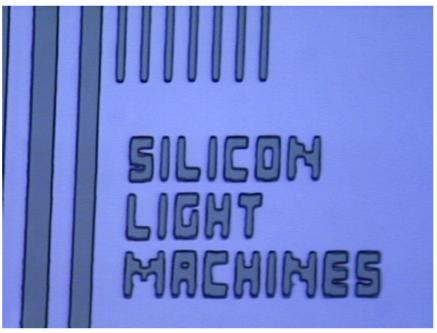
MAS:Minimum Address Size

GLV Maskless Lithography





- 355nm exposure
- I-line resist
- 2 micron resolution



Wafer Direct Imaging





- 300 mm wafer
- 2.5 um resolution

Sample wafer courtesy of Dainippon Screen R&D Center